Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

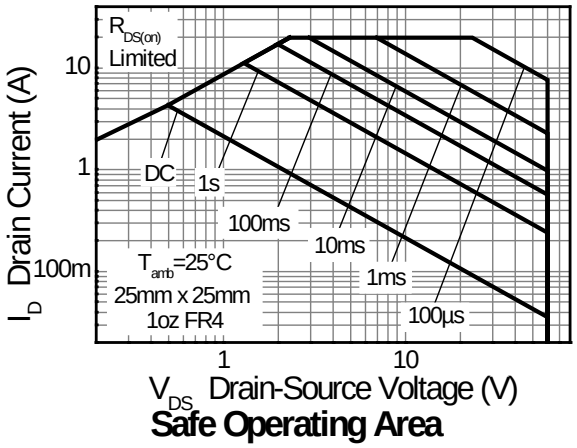
Characteristic			Symbol	Value	Unit
Drain-Source voltage			V_{DSS}	60	V
Gate-Source voltage		(Note 5)	V_{GS}	±20	V
Single Pulsed Avalanche Energy		(Note 11)	E_{AS}	37.5	mJ
Single Pulsed Avalanche Current		(Note 11)	I_{AS}	5.0	A
Continuous Drain current	V_{GS} = 10V	(Note 7)	I_D	8.5	A
		T_A = 70°C (Note 7)		6.8	
		(Note 6)		6.0	
Pulsed Drain current	V_{GS}= 10V	(Note 8)	I_{DM}	22.2	A
Continuous Source current (Body diode)		(Note 7)	I_S	10.2	A
Pulsed Source current (Body diode)		(Note 8)	I_{SM}	22.2	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

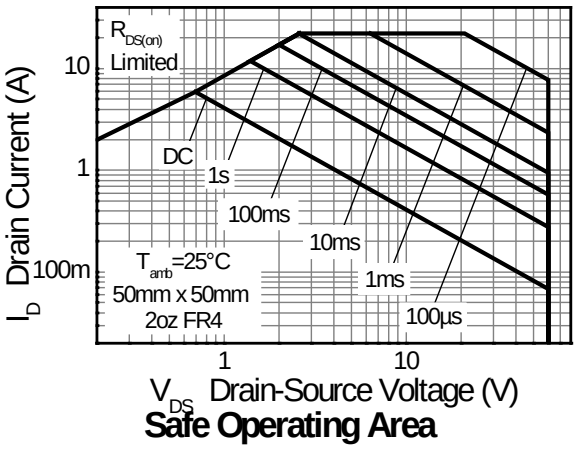
Characteristic		Symbol	Value	Unit
Power dissipation Linear derating factor	(Note 6)	P_D	4.12 33	W mW/°C
	(Note 7)		8.49 67.9	
	(Note 9)		2.12 16.9	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	30.3	°C/W
	(Note 7)		14.7	
	(Note 9)		59.0	
Thermal Resistance, Junction to Lead	(Note 10)	$R_{\theta JL}$	3.09	
Operating and storage temperature range		T_J, T_{STG}	-55 to +150	°C

Notes:
5. AEC-Q101 V_{GS} maximum is ±16V.
6. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
7. Same as note 2, except the device is measured at t ≤ 10 sec.
8. Same as note 2, except the device is pulsed with D = 0.02 and pulse width 300 µs. The pulse current is limited by the maximum junction temperature.
9. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
10. Thermal resistance from junction to solder-point (at the end of the drain lead).
11. UIS in production with L = 3.0mH, I_{AS} = 5.0A, R_G = 25• , V_{DD} = 50V, starting T_J = 25°C

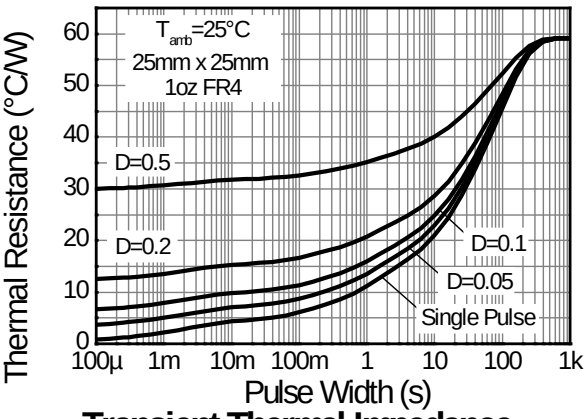
Thermal Characteristics



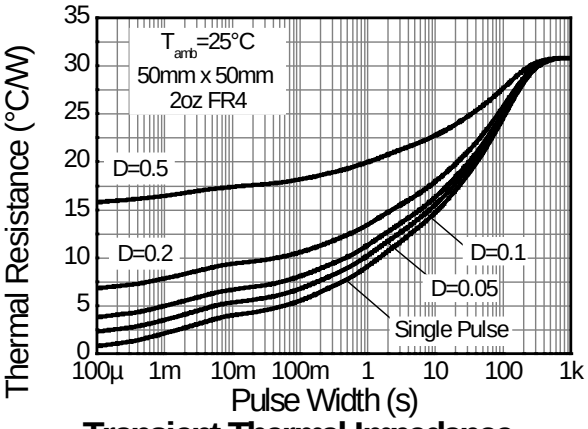
Safe Operating Area



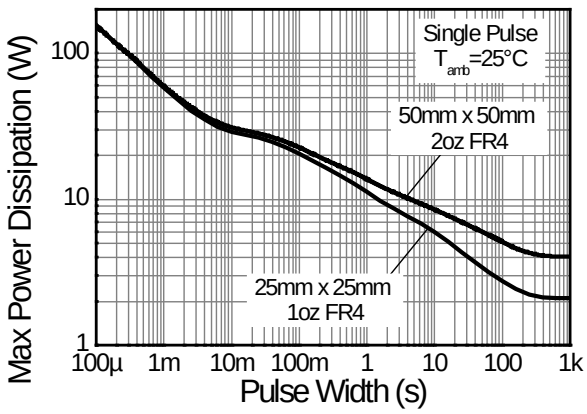
Safe Operating Area



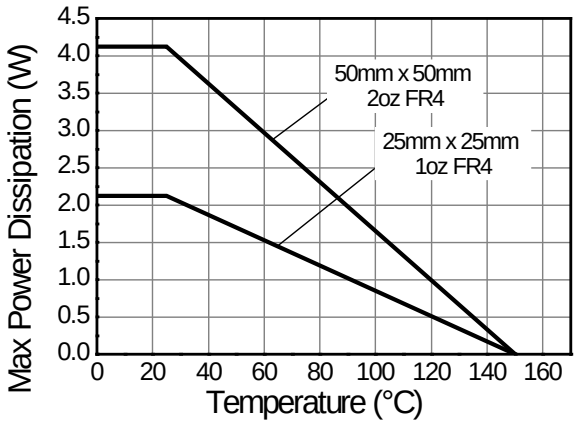
Transient Thermal Impedance



Transient Thermal Impedance



Pulse Power Dissipation



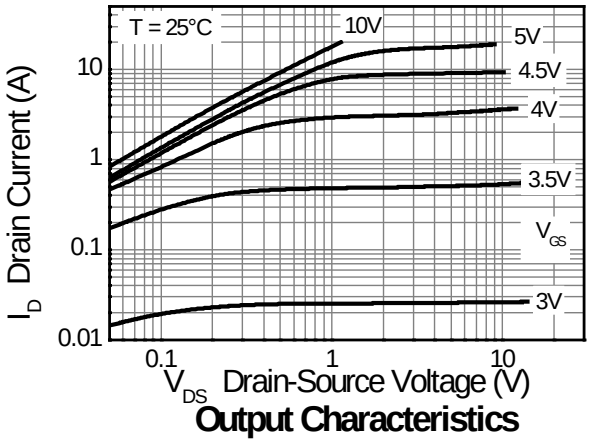
Derating Curve

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

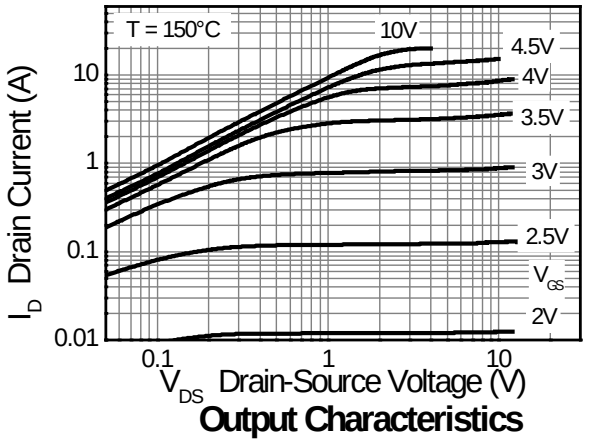
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	I_D = 250μA, V_{GS}= 0V
Zero Gate Voltage Drain Current	I_{DSS}	—	—	0.5	μA	V_{DS}= 60V, V_{GS}= 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS}= ±20V, V_{DS}= 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	—	3.0	V	I_D= 250μA, V_{DS}= V_{GS}
Static Drain-Source On-Resistance (Note 12)	$R_{DS\ (ON)}$	—	—	0.068	Ω	V_{GS}= 10V, I_D= 12A
				0.100		V_{GS}= 4.5V, I_D= 6A
Forward Transconductance (Notes 12 & 13)	g_{fs}	—	19.7	—	S	V_{DS}= 15V, I_D= 12A
Diode Forward Voltage (Note 12)	V_{SD}	—	0.98	1.15	V	I_S= 12A, V_{GS}= 0V
Reverse recovery time (Note 13)	t_{rr}		145	—	ns	I_S= 12A, di/dt= 100A/μs
Reverse recovery charge (Note 13)	Q_{rr}	—	929	—	nC	
DYNAMIC CHARACTERISTICS (Note 13)						
Input Capacitance	C_{iss}	—	502	—	pF	V_{DS}= 30V, V_{GS}= 0V f= 1MHz
Output Capacitance	C_{oss}	—	45.7	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	27.1	—	pF	
Total Gate Charge	Q_g	—	5.55	—	nC	V_{GS}= 4.5V; V_{DS}= 30V, I_D= 12A
Total Gate Charge	Q_g	—	10.3	—	nC	V_{GS}= 10V; V_{DS}= 30V, I_D= 12A
Gate-Source Charge	Q_{gs}	—	1.6	—	nC	
Gate-Drain Charge	Q_{gd}	—	3.5	—	nC	
Turn-On Delay Time (Note 14)	$t_{D(on)}$	—	3.6	—	ns	V_{DD}= 30V, V_{GS}= 10V I_D= 12A, $R_G \cong 6.0\Omega$
Turn-On Rise Time (Note 14)	t_r	—	10.8	—	ns	
Turn-Off Delay Time (Note 14)	$t_{D(off)}$	—	11.9	—	ns	
Turn-Off Fall Time (Note 14)	t_f	—	8.7	—	ns	

Notes: 12. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
13. For design aid only, not subject to production testing.
14. Switching characteristics are independent of operating junction temperatures.

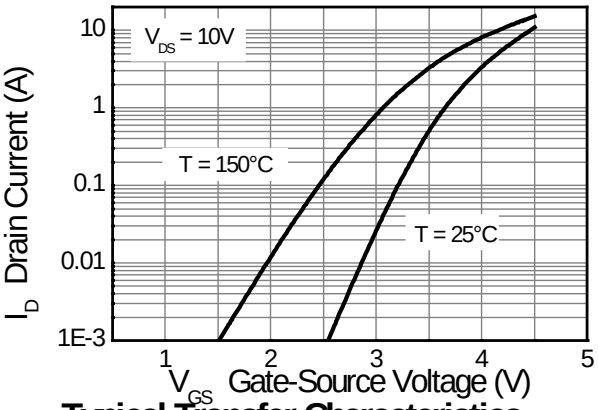
Typical Characteristics



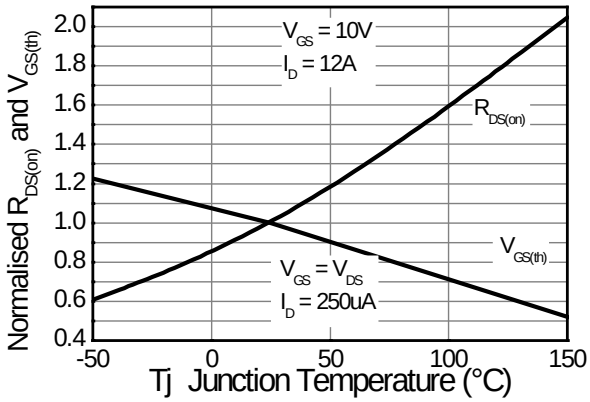
Output Characteristics



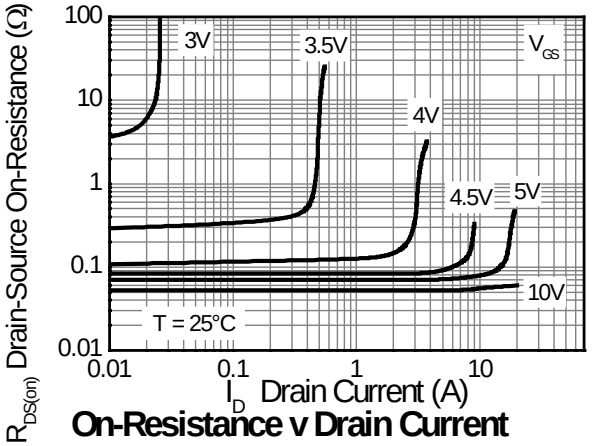
Output Characteristics



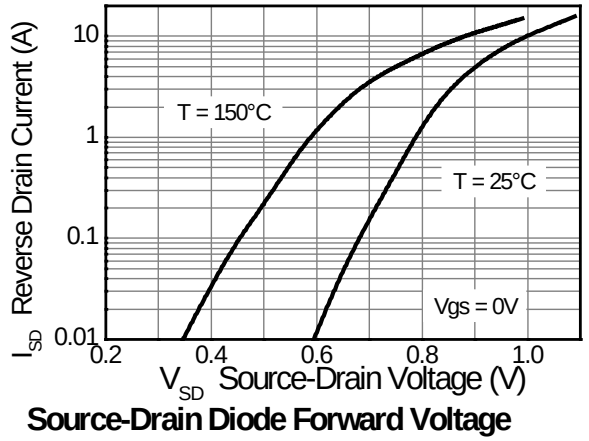
Typical Transfer Characteristics



Normalised Curves v Temperature

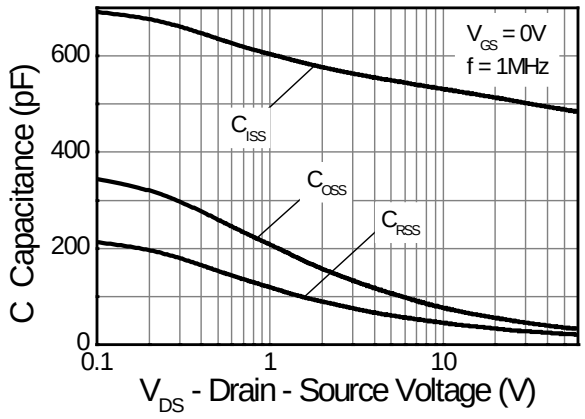


On-Resistance v Drain Current

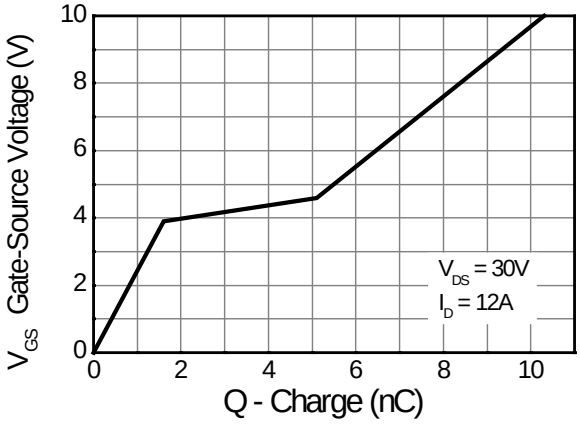


Source-Drain Diode Forward Voltage

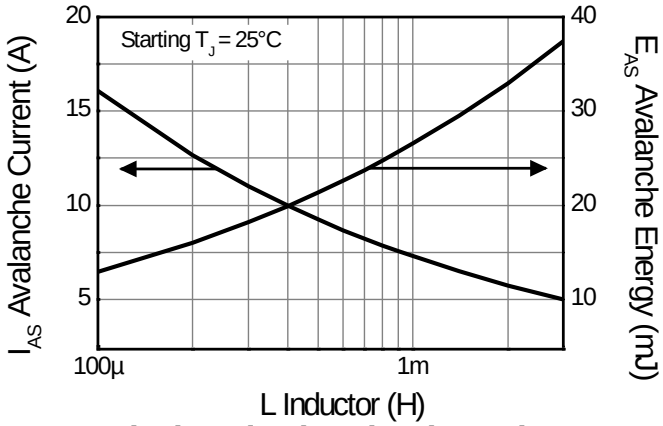
Typical Characteristics - continued



Capacitance v Drain-Source Voltage

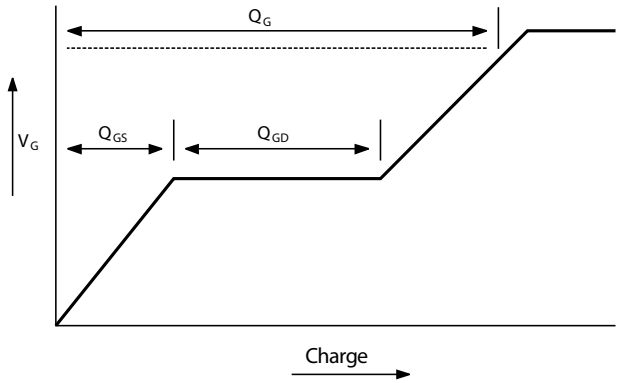


Gate-Source Voltage v Gate Charge

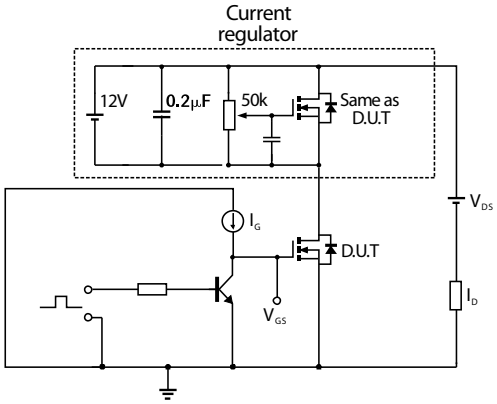


Single-Pulsed Avalanche Rating

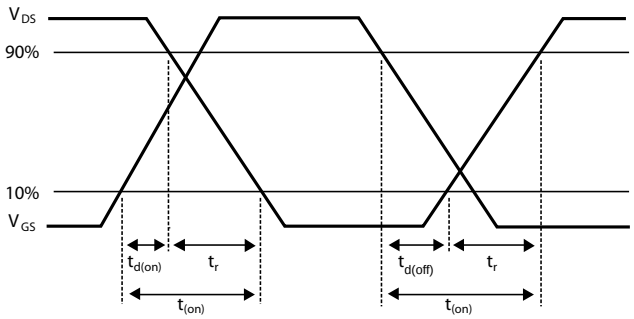
Test Circuits



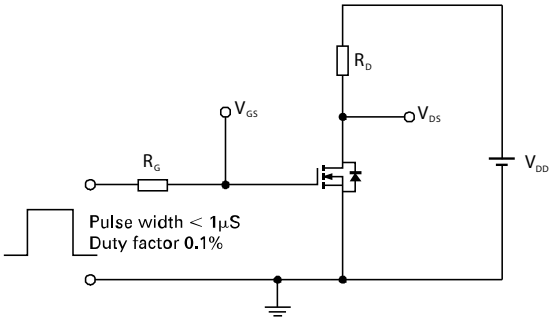
Basic gate charge waveform



Gate charge test circuit



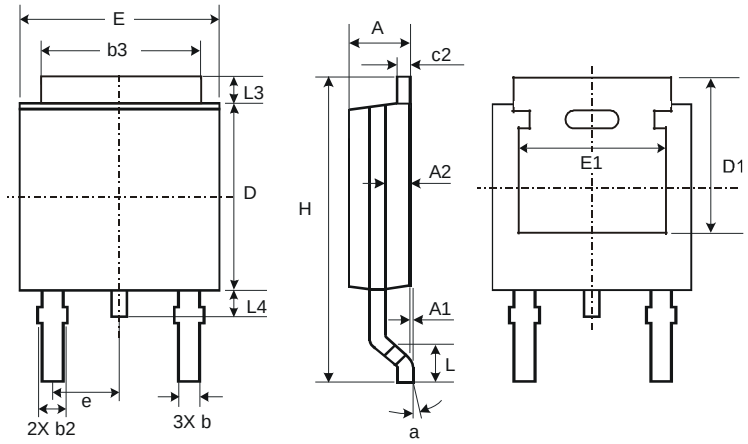
Switching time waveforms



Switching time test circuit

Package Outline Dimensions

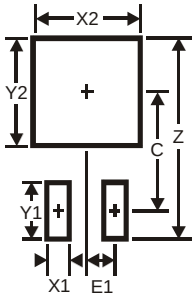
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



TO252			
Dim	**Min**	**Max**	**Typ**
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c2	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	–	–
e	–	–	2.286
E	6.45	6.70	6.58
E1	4.32	–	–
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	–
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
C	6.9
E1	2.3